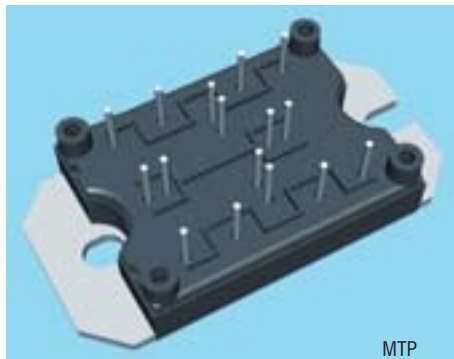


Insulated Gate Bipolar Transistors (IGBTs) - continued

SIP Modules - continued

Mftrs. List No.	Order Code	1+	25+	100+
CPV363M4F	166-078▲	2,407.00	2,115.00	1,915.00
CPV363M4FPBF	910-1900●	3,699.00	2,722.00	2,117.00
CPV364M4K	167-812▲	3,441.00	2,566.00	--
CPV364M4KPBF	910-1918●	3,699.00	2,722.00	2,117.00
CPV364M4U	167-824▲	3,699.00	2,722.00	2,250.00

IGBT Modules



International IGR Rectifier

- Modules combining high-speed IGBTs with optimised diodes
- Single package offers space and assembly-cost savings compared to discrete solutions
- Fully isolated modules are insulated with a ceramic nitride layer for improved thermal conductivity

Configuration	V _{CES} V	I _C @ T _c =25°C A	I _C pulsed A	V _{CE(sat)} max. V	@ I _C A	P _D @ T _c =25°C W	Mftrs. List No.
Full Bridge	1200	40	100	3.59	20	240W*	20MT120UFPBF
Half Bridge	600	114	350	3.15	50	658W	50MT060WHPBF
Half Bridge	1200	80	160	3.59	40	463W*	40MT120UHPBF

*Excludes Diode

Mftrs. List No.	Order Code	1+	25+	100+	250+
20MT120UFPBF	910-1888●	4,144.00	3,050.00	2,372.00	2,098.00
40MT120UHPBF	910-1896●	4,256.00	3,132.00	2,436.00	2,154.00
50MT060WHPBF	910-1926●	2,800.00	2,144.00	1,975.00	--

High Performance Power Modules

Fuji Electric Device Technology Co., Ltd.



- High speed switching
- Single or half-bridge configurations
- Additional S-Series Features:**
- NPT Technology options (S-Series)
- Square short-circuit SOA at 10 x I_C
- High short-circuit withstand capability
- Low loss
- Soft switching

Package	H	W	D	Package	H	W	D
M127	35	108	62	M234	30	108	62
M138	35	110	80	M235	30	108	62
M232	30	92	34	M236	30	110	80
M233	30	92	45				

V _{CES} V	I _C @ T _c =25°C A	I _C pulsed A	V _{CE(sat)} max. V	@ I _C A	t _r max. ns	t _f max. ns	P _D @ T _c =25°C W	Package	Mftrs. List No.
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Half-Bridge Configuration, N-Series									
600	50	100	2.8	50	600	350	250	M232	2MBI50N-060
600	75	150	2.8	75	600	350	320	M232	2MBI75N-060
600	100	200	2.8	100	600	350	400	M232	2MBI100N-060
600	150	300	2.8	150	600	350	600	M233	2MBI150N-060
600	200	400	2.8	200	600	350	780	M233	2MBI200N-060
600	300	600	2.8	300	600	350	1100	M233	2MBI300N-060
600	400	800	2.8	400	600	350	1500	M235	2MBI400N-060

Single Switch Configuration, Non-Punch Through S-Series									
1200	300	600	2.6	200	600	300	1500	M127	1MBI200S-120
1200	400	800	2.6	200	600	300	2100	M127	1MBI300S-120
1200	600	1200	2.6	400	600	300	3100	M127	1MBI400S-120
1200	900	1800	2.6	600	600	300	4150	M138	1MBI600S-120

Half-Bridge Configuration, Non-Punch Through S-Series									
1200	100	200	2.6	75	600	300	600	M232	2MBI75S-120
1200	100	300	2.6	75	600	300	780	M234	2MBI100S-120
1200	200	400	2.6	150	600	300	1000	M234	2MBI150S-120
1200	300	600	2.6	200	600	300	1500	M234	2MBI200S-120
1200	400	800	2.6	300	600	300	2500	M236	2MBI300S-120

Mftrs. List No.	Order Code	1+	3+	10+
Half-Bridge, N-Series				
2MBI50N-060	120-8663●	3,700.00	2,948.00	2,333.00
2MBI100N-060	120-8665●	4,395.00	3,505.00	2,771.00
2MBI150N-060	120-8666●	8,557.00	6,826.00	5,395.00
2MBI200N-060	120-8667●	10,254.00	8,179.00	6,464.00
2MBI400N-060	120-8668●	16,575.00	13,222.00	10,448.00
Single-Bridge, S-Series				
1MBI200S-120	120-8669●	8,595.00	6,856.00	5,419.00
1MBI400S-120	120-8670●	13,067.00	10,423.00	8,238.00
1MBI600S-120	120-8671●	25,053.00	19,987.00	15,795.00
Half-Bridge, S-Series				
2MBI75S-120	120-8672●	5,782.00	4,612.00	3,645.00
2MBI100S-120	120-8673●	7,786.00	6,210.00	4,907.00
2MBI150S-120	120-8674●	10,793.00	8,610.00	6,804.00
2MBI200S-120	120-8677●	14,647.00	11,685.00	9,236.00

Power Modules



INT-A-PAK

V _{CES} V	I _C @ T _c =25°C A	I _C pulsed A	V _{CE(sat)} max. V	@ I _C A	t _r typ. ns	t _f typ. ns	P _D @ T _c =25°C W	Package	Mfr.	Mftrs. List No.
Single Switch Configuration										
Half-Bridge Configuration										
600	75	150	2.2	75	94	180	285	INT-A-PAK	IR	GA75TS60U
600	250	500	2.3	250	242	190	780	INT-A-PAK	IR	GA250TS60U
1200	75	150	3.1	75	119	402	390	INT-A-PAK	IR	GA75TS120U

Half-Bridge Configuration, Double INT-A-PAK										
600	400	800	2.4	400	335	225	1250	DOUBLE INT-A-PAK	IR	GA400TD60U
600	500	1000	2.4	500	430	190	1550	DOUBLE INT-A-PAK	IR	GA250TD60U
1200	250	500	2.9	250	227	343	1250	DOUBLE INT-A-PAK	IR	GA250TD120U

21151

Mftrs. List No.	Order Code	1+	25+	100+
GA75TS120U	167-861▲	6,523.00	5,267.00	--
GA75TS60U	393-9480▲	4,579.00	3,770.00	3,299.00
GA250TD120U	393-9431▲	17,228.00	14,452.00	12,288.00
GA250TS60U	393-9443▲	10,643.00	7,982.00	6,785.00
GA400TD60U	393-9467▲	16,010.00	12,007.00	10,206.00
GA500TD60U	393-9479▲	20,140.00	15,105.00	12,839.00

Semiconductors - Discretes

21

Low Power MOSFETs

Digital FETs



- Easy to drive
- Replacements for digital bipolar transistors
- Suitable for 5V and 3V logic signals
- >6kV ESD protected
- Industry standard SOT-23 package
- No additional bias resistors required

FAIRCHILD SEMICONDUCTOR

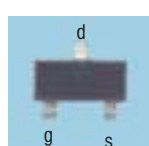


V _{DS} V	N/P Channel	R _{DS(on)} @ 2.7V, Ω	I _D A	I _D pulsed A	V _{GS(th)} V	P _D W	Device I.D.	Mftrs. List No.
25	N	0.6	0.68	2	1.5	0.35	303	FDV303N
25	N	5	0.22	0.5	1.5	0.35	301	FDV301N
25	P	1.5	0.46	0.5	1.5	0.35	304P	FDV304P
25	P	13	0.12	0.5	1.5	0.35	302P	FDV302P

211305

Mftrs. List No.	Order Code	1+	10+	100+	250+
FDV303N	984-5020●	19.00	15.00	12.00	8.00
FDV301N	984-5011●	13.00	10.00	8.00	5.00
FDV304P	984-6123●	28.00	22.00	17.00	11.00
FDV302P	984-6115●	12.00	10.00	7.00	4.00

SOT-23



H=1.12, W=3.05, D=2.5

Supplied on 8mm tape.



Footprint

V _{DS} V	R _{DS(on)} Ω	I _{D cont} @ 25°C A	I _D pulsed A	V _{GS(th)} max. (*min) V	P _D @ 25°C W	Mfr.	Device Marking	Mftrs. List No.
N Channel								
20	1	0.3	0.75	3	0.2	SLX	N1	TN0201T
20	1	0.42	0.8	3.0	0.35	SLX	K3	TN0201K
20	0.4	0.73	4	1	0.35	SLX	K2ywl*	TN0200K
20	0.25	4.2	33.0	1.2	1.25	IR	1G	IRLML2502PBF